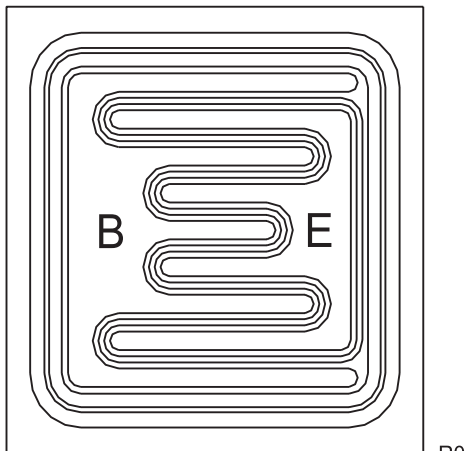


PROCESS DETAILS

Process	EPITAXIAL BASE
Die Size	66 X 66 MILS
Die Thickness	12.5 ± 1.0 MILS
Base Bonding Pad Area	12 X 24 MILS
Emitter Bonding Pad Area	11 X 14 MILS
Top Side Metalization	Al - 50,000Å
Back Side Metalization	Cr/Ni/Ag - 16,000Å

GEOMETRY



BACKSIDE COLLECTOR

R0

GROSS DIE PER 4 INCH WAFER

2,630

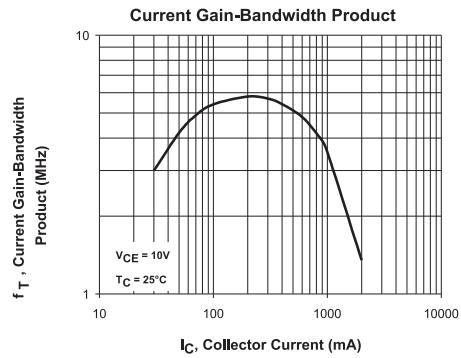
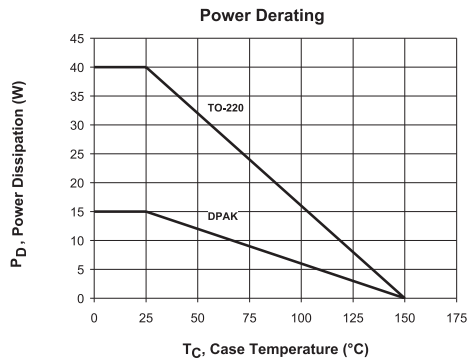
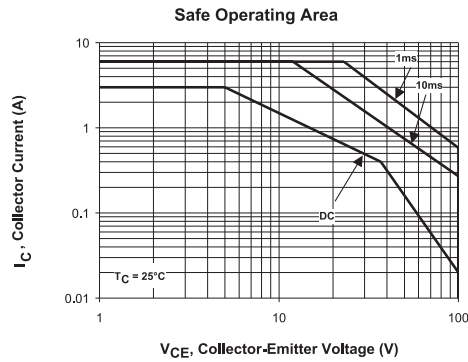
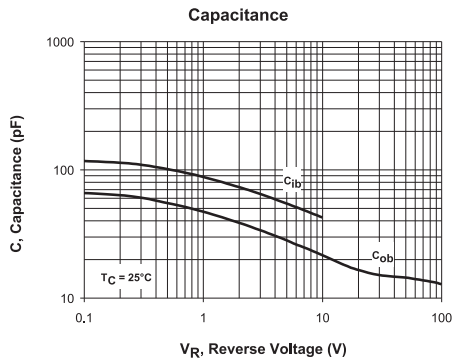
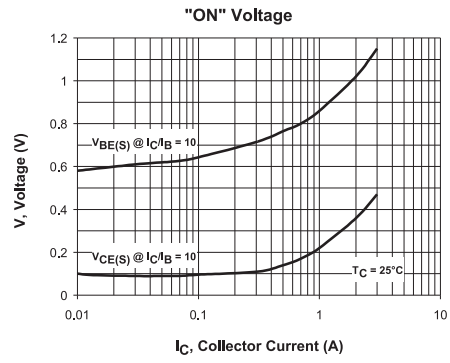
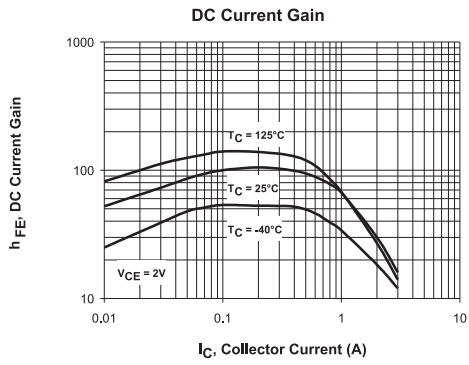
PRINCIPAL DEVICE TYPES

CJD32C

TIP32C

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R2 (1-August 2002)



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